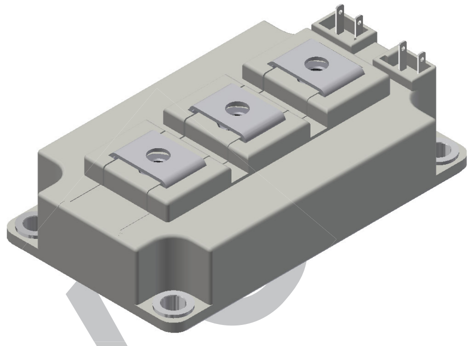
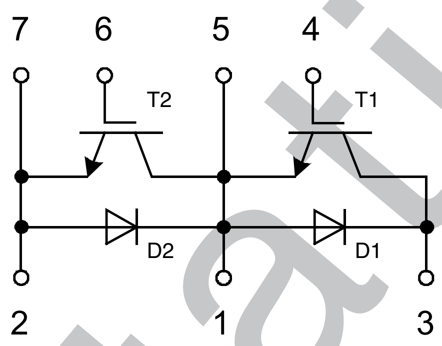
IGBT Module

V_{CES}	= 1700 V
I_{C25}	= 325 A
$V_{CE(sat)}$	= 1.90 V

Phase leg



Part number
MITH250PF1700LP



Features / Advantages:

- Trench IGBT
  - low $V_{CE(sat)}$
  - easy paralleling due to the positive temperature coefficient of the on-state voltage
  - Tvjm = 175°C
  - square RBSOA @ 2x Ic
  - short circuit rated for 10 µsec.
  - low gate charge
  - low EMI
- Free wheeling diode
  - fast and soft reverse recovery
  - low operating forward voltage

Applications:

- AC motor drives
- Solar inverter
- Air-conditioning systems
- high power converters
- UPS

Package: Y3-M6

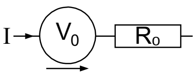
- Isolation Voltage: 4000 V~
- Industry standard outline
- RoHS compliant
- Copper base plate
- internally DCB isolated
- ultrasonic welded power terminals
- advanced power cycling

IGBT T1, T2				Ratings			
Symbol	**Definitions**	**Conditions**		**min.**	**typ.**	**max.**	
V_{CES}	*collector emitter voltage*		T_{VJ} = 25°C			1700	V
V_{GES}	*max. DC gate voltage*			-20		+20	V
I_{C25}	*collector current*		T_C = 25°C			325	A
I_{C80}			T_C = 80°C			250	A
I_{CRM}	*repetitive peak collector current*	Pulse width and repetition rate should not be such that device junction temperature (T_J) does not exceed the max. rating of 175°C				600	A
P_{tot}	*total power dissipation*		T_C = 25°C			1215	W
$V_{CE(sat)}$	*collector emitter saturation voltage*	I_C = 200 A; V_{GE} = 15 V	T_{VJ} = 25°C		1.90	2.20	V
		on die level	T_{VJ} = 150°C		2.30		V
		I_C = 200 A; V_{GE} = 15 V	T_{VJ} = 25°C		2.00	2.30	V
		between power terminals	T_{VJ} = 150°C		2.40		V
$V_{GE(th)}$	*gate emitter threshold voltage*	I_C = 8 mA; V_{CE} = V_{GE}	T_{VJ} = 25°C	5.2	5.8	6.4	V
I_{CES}	*collector emitter leakage current*	V_{CE} = 1700 V; V_{GE} = 0 V	T_{VJ} = 25°C			2.7	mA
			T_{VJ} = 150°C		3.5		mA
I_{GES}	*gate emitter leakage current*	V_{GE} = ±20 V; V_{CE} = 0 V				1200	nA
R_G	*internal gate resistance*				3.75		Ω
C_{iss}	*input capacitance*	V_{CE} = 25 V; V_{GE} = 0 V; f = 1 MHz	T_{VJ} = 25°C		18		nF
C_{oss}	*output capacitance*				680		pF
C_{rss}	*reverse transfer (Miller) capacitance*				580		pF
Q_g	*total gate charge*	V_{CE} = 900 V; V_{GE} = -8 V/15 V; I_C = 200A			1600		nC
Q_{gs}	*gate source charge*						nC
Q_{gd}	*gate drain (Miller) charge*						nC
$t_{d(on)}$	*turn-on delay time*	Inductive switching V_{CE} = 1200 V; I_C = 200 A V_{GE} = ±15 V; R_G = 2.0 Ω (external)	T_{VJ} = 150°C		260		ns
t_r	*current rise time*				35		ns
$t_{d(off)}$	*turn-off delay time*				710		ns
t_f	*current fall time*				150		ns
E_{on}	*turn-on energy per pulse*				69		mJ
E_{off}	*turn-off energy per pulse*				79		mJ
$E_{rec(off)}$	*reverse recovery losses at turn-off*						mJ
SCSOA	*short circuit safe operating area*	V_{CEmax} = 1700 V					
t_{SC}	*short circuit duration*	V_{CE} = 720 V; V_{GE} = ±15 V	T_{VJ} = 150°C			10	µs
I_{SC}	*short circuit duration*	non-repetitive					A
R_{thJC}	*thermal resistance junction to case*	per IGBT				0.123	K/W
R_{thJH}	*thermal resistance junction to heatsink*	with heatsink compound; IXYS test setup			0.17		K/W

Diode D1, D2

Symbol	Definitions	Conditions		min.	typ.	max.	
V_{RRM}	*max. repetitive reverse voltage*		T_{VJ} = 25°C			1700	V
I_{F25}	*forward current*		T_C = 25°C			205	A
I_{F80}			T_C = 80°C			151	A
V_F	*forward voltage*	I_F = 200 A; V_{GE} = 0 V	T_{VJ} = 25°C		2.00	2.40	V
		on die level	T_{VJ} = 150°C		2.15		V
		I_F = 200 A; V_{GE} = 0 V	T_{VJ} = 25°C		2.10	2.50	V
		between power terminals	T_{VJ} = 150°C		2.25		V
I_R	*reverse current*	$V_R = V_{RRM}$	T_{VJ} = 25°C			*	mA
	* not applicable, see Ices at IGBT		T_{VJ} = 150°C		*		mA
Q_{RM}	*reverse recovery charge*	V_R = 1200 V, I_F = 200 A,	T_{VJ} = 25°C		50		µC
I_{RM}	*max. reverse recovery current*				200		A
t_{rr}	*reverse recovery time*	-di$_F$/dt = 3200 A/µs					ns
E_{rec}	*reverse recovery energy*				23		mJ
Q_{RM}	*reverse recovery charge*	V_R = 1200 V, I_F = 200 A,	T_{VJ} = 125°C		90		µC
I_{RM}	*max. reverse recovery current*				260		A
t_{rr}	*reverse recovery time*	-di$_F$/dt = 3200 A/µs					ns
E_{rec}	*reverse recovery energy*				50		mJ
R_{thJC}	*thermal resistance junction to case*					0.28	K/W
R_{thJH}	*thermal resistance junction to heatsink*	with heatsink compound; IXYS test setup			0.39		K/W

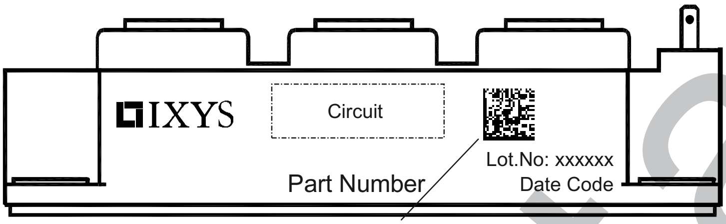
Equivalent Circuits for Simulation *on die level



			IGBT T1, T2	Diode D1, D2	
$V_{0\,max}$	*threshold voltage*	T_{VJ} = 150°C	0.8	1.08	V
$R_{0\,max}$	*slope resistance* *		9.0	5.4	mΩ
$V_{0\,max}$	*threshold voltage*	T_{VJ} = 175°C			V
$R_{0\,max}$	*slope resistance* *				mΩ

IXYS reserves the right to change limits, test conditions and dimensions. 20160621

Package Y3-M6			Ratings			
Symbol	**Definitions**	**Conditions**	**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal			300	A
T_{stg}	*storage temperature*		-40		125	°C
T_{op}	*operation temperature*		-40		150	°C
T_{VJ}	*virtual junction temperature*		-40		175	°C
Weight					340	g
M_S	*mounting torque for screws to heatsink*	M6 to heatsink	3		5	Nm
M_T	*mounting torque for terminal screws*	M6 to terminals	2.5		5	Nm
V_{ISOL}	*isolation voltage*	t = 1 minute, 50 / 60 Hz, RMS	4000			V
$R_{terminal\text{-}chip}$	*resistance terminal to chip*			0.5		mΩ
C_P	*coupling capacity per switch*	between shorted pins of switch and back side metallization				pF



Data Matrix: *Typ* (1-19), DC+*Prod.Index* (20-25), *FKT#* (26-31)
leer (33), *lfd.#* (33-36)

Part number

M = Module
I = IGBT
T = Trench IGBT
H = Gen 5
250 = Current Rating [A]
PF = phase leg
1700 = Reverse Voltage [V]
LP = Y3-M6

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MITH250PF1700LP	MITH250PF1700LP			

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Outlines Y3-M6